

RAYCONN ELECTRONICS CO., LTD.

SPECIFICATION FORM

FEATURES

- ◇ 30.10MM×16.0MM OUTLINE
- ◇ 0.4 INCHES (10.20MM) DIGIT HEIGHT
- ◇ THREE DIGIT
- ◇ SINGLE COLOR
- ◇ HIGH BRIGHTNESS
- ◇ EASY ASSEMBLY
- ◇ SOLID STATE RELIABILITY

DESCRIPTION

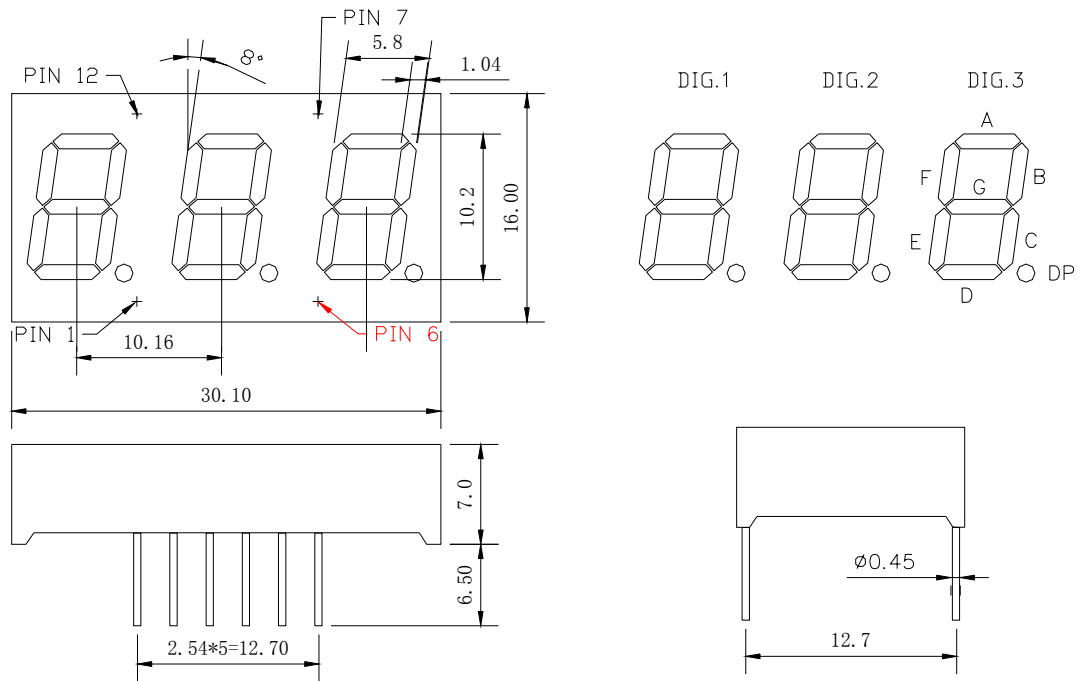
The REC-S4301AG-3 is a 0.4 inches (10.20mm) digit height, 30.10mm×16.0mm outline, single color, three digit, common anode numeric display. This display utilizes green LED chips fabricated from GaP epiwafer on GaP substrate grown by liquid phase epitaxy. The devices have black face and white segments.

DEVICE

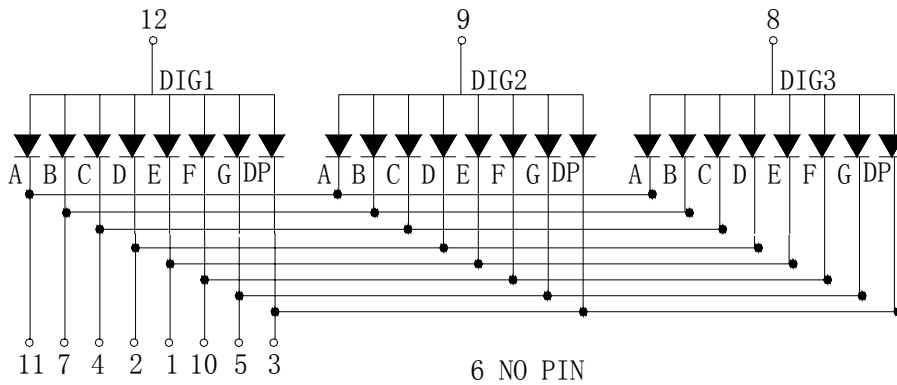
PART NO.	EMITTING COLOR	DESCRIPTION
REC-S4301AG-3	Yellow-Green	Black face, White Segments.

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PACKAGE DIMENSION



INTERNAL CIRCUIT DIAGRAM



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PIN CONNECTION

PIN NO.	CONNECTION	PIN NO.	CONNECTION
1	Anode E	7	Anode B
2	Anode D	8	Cathode
3	Anode DP	9	Cathode
4	Anode C	10	Anode F
5	Anode G	11	Anode A
6	NO PIN	12	Cathode

ABSOLUTE MAXIMUM RATING AT $T_A = 25^\circ\text{C}$

PARAMETER	SYMBOL	MAXIMUM	UNIT
Power Dissipation per dot	P_{AD}	75	mW
Peak Forward Current per dot (1/10 duty cycle, 0.1ms pulse width)	I_{PF}	80	mA
Continuous Forward Current per dot	I_{AF}	20	mA
Reverse Voltage per dot	V_R	5	V
Operating Temperature Range, T_{opr}	- 25° C to + 80° C		
Storage Temperature Range, T_{stg}	- 30° C to + 85° C		
Solder Temperature : 1 / 16 inch below seating plane for 3 seconds at 260° C			

ELECTRO - OPTICAL CHARACTERISTICS AT $T_A = 25^\circ\text{C}$

PARAMETER	UNIT	MIN	TYPE	MAX
Luminous Intensity per chip, I_V ($I_F=20\text{mA}$)	mcd	9	12	15
Peak Emission Wavelength, λ_p ($I_F=20\text{mA}$)	nm		571	
Special Line Half-Width, $\Delta\lambda$ ($I_F=20\text{mA}$)	nm		30	
Forward Voltage per chip, V_F ($I_F=20\text{mA}$)	V	1.8	2.15	2.5
Reverse Current per chip, I_R , ($V_R=5\text{V}$)	μA			100
Luminous Intensity Matching Ratio, I_{V-m} ($I_F=20\text{mA}$)				2:1